

Abstract

METHOD FOR PRODUCING POLYSILICON ROD

A resistivity value of a polysilicon rod deposited in an initial period of a growth period is improved, while preventing collapse of the rod in the initial period. A polysilicon rod production method supplies, to a silicon core wire erected inside a reaction furnace (10) and heated by energization, a raw material gas (G1) containing chlorosilanes to deposit polysilicon on the wire surface to grow the polysilicon into a polysilicon rod (S1) of not less than 80 mm in diameter, the method including: introducing the gas into the furnace such that the number of gas exchanges, which is an amount of the gas introduced into the furnace relative to a volume of the furnace, in a growth start period (T1) of the rod, which lasts until one hour elapses from a start of the deposition on the wire surface, is not less than 8 times and less than 35 times.

(Fig. 1)